HN62W448NI Series

524288-word × 16-bit/1048576-word × 8-bit CMOS Mask Programmable ROM

HITACHI

ADE-203-769A (Z)
Rev. 1.0
Apr. 22, 1997

Description

The Hitachi HN62W448NI series is a 8-Mbit CMOS mask-programmable ROM organized either as 524288-word × 16-bit or as 1048576-word × 8-bit. It has realized high speed normal access 120 ns and page mode access 50 ns on 3.3 V supply. It is the most suitable to the program and data memory for low voltage potable system. It has package variations of standard 42-pin plastic DIP and standard 44-pin plastic SOP.

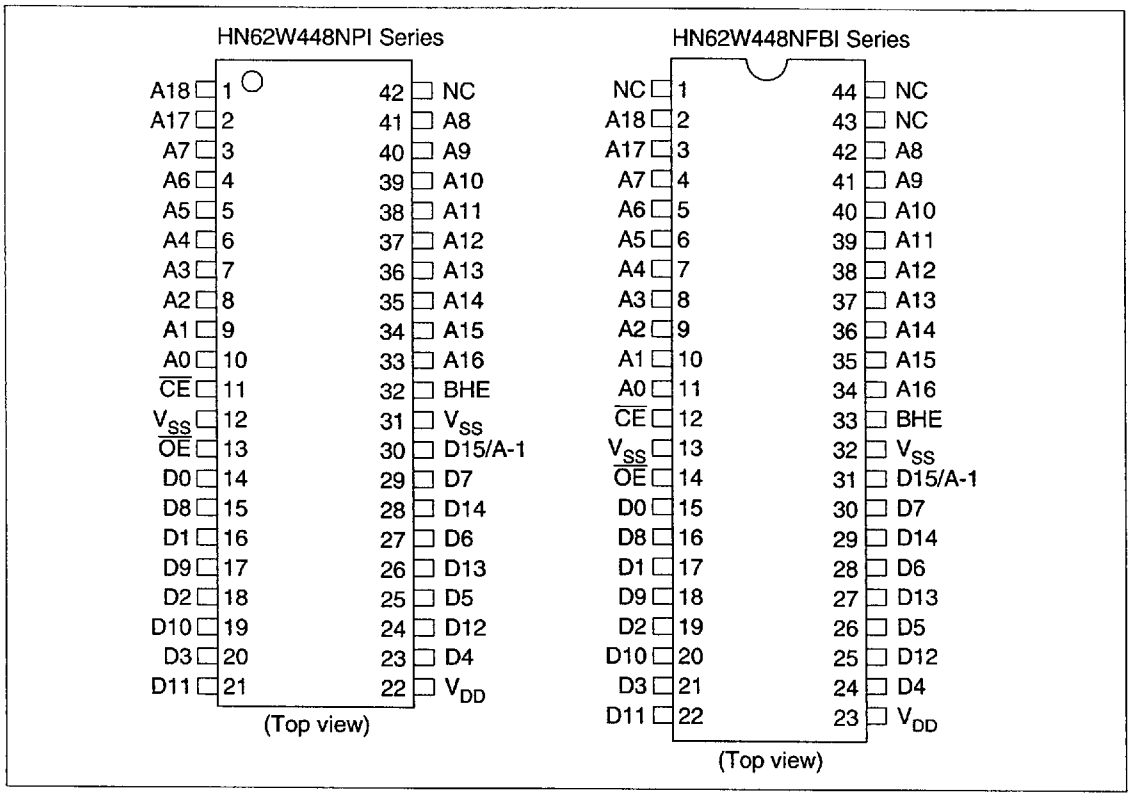
Features

- Single 3.3 V supply : 3.3 V ± 0.3 V
- Access time:
  - — Normal access time: 120 ns (max)
  - — Page access time: 50 ns (max)
- Power dissipation
  - — Active: 216 mW (max)
  - — Standby: 108 µW (max)
- Byte-wide or word-wide data organization with byte/word selection (BHE)
- 4-word page access on word-wide mode
- 8-byte page access on byte-wide mode
- Three-state data output for wired or-tying
- Directly TTL compatible all inputs and outputs
- Operating temperature rage: –40 to +85°C

Ordering Information

Type No.	Access time	Package
HN62W448NPI-12	120 ns	600mil 42-pin plastic DIP (DP-42)
HN62W448NFBI-12	120 ns	600mil 44-pin plastic SOP (FP-44D)

Pin Arrangement



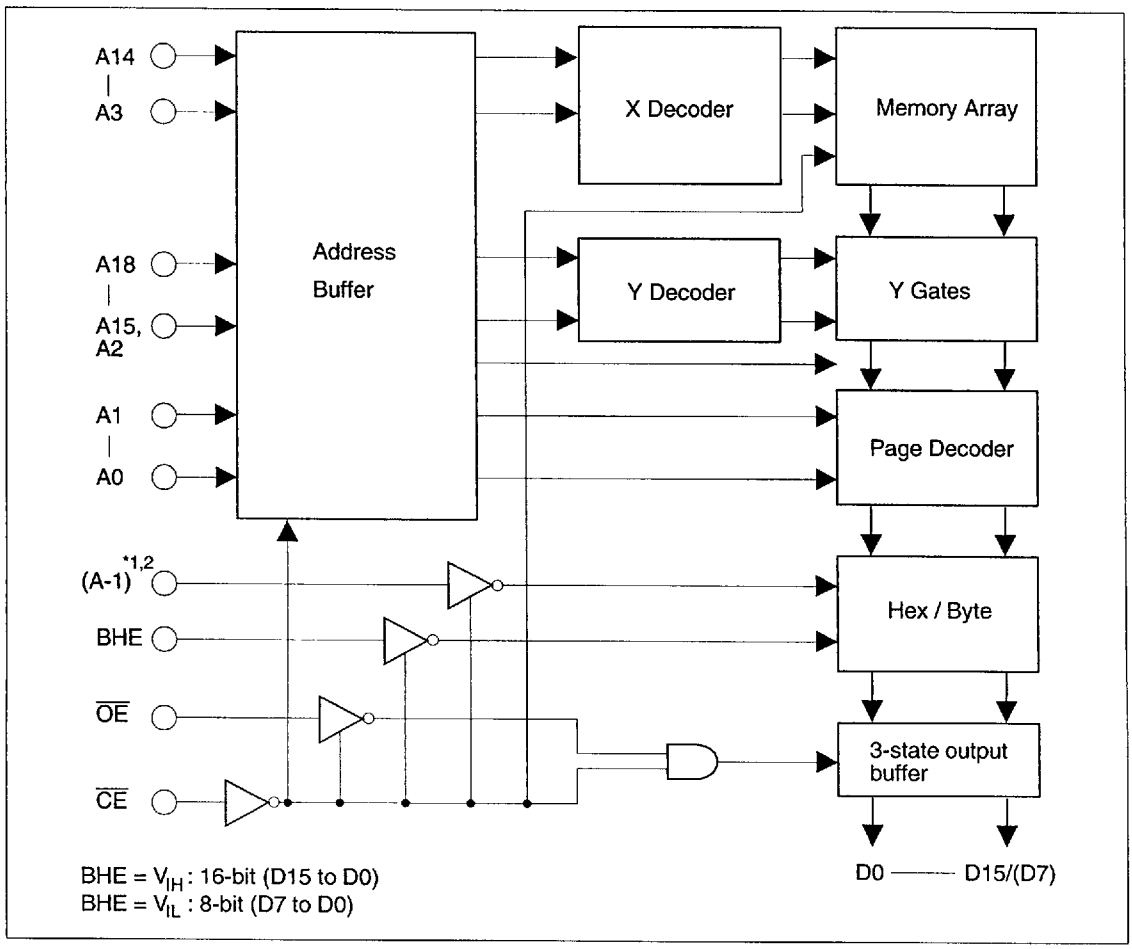
Pin Description

Pin name	Function
A2 to A18	Address input
A-1, A0, A1	Page address input
D0 to D15	Data output
$\overline{OE}$	Output enable
$\overline{CE}$	Chip enable
BHE	Byte/word selection
V_{DD}	Power supply
V_{SS}	Ground
NC	No connection

Block Diagram

Notes: 1. A-1 is least significant address.

2. When BHE is 'low', D14 to D8 goes the high impedance state, and D15 should be A-1.



Mode Selection

	Pin							
					Data output		Address input	
Mode	$\overline{CE}$	$\overline{OE}$	BHE	D15/A-1	D0-D7	D8-D15	LSB	MSB
Standby	H	×[*1]	×	×	High-Z	High-Z	—	—
Output disable	L	H	×	×	High-Z	High-Z	—	—
Read (16-bit)	L	L	H	Dout	D0 to D7	D8 to D15	A0	A18
Read (8-bit)	L	L	L	L	D0 to D7	High-Z	A-1	A18
Read (8-bit)	L	L	L	H	D8 to D15	High-Z	A-1	A18

Note: 1. ×: Don't care.

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to V_{SS}	V_{DD}	–0.3 to +5.5	V
All input and output voltage relative to V_{SS}	Vin, Vout	–0.3 to V_{DD} +0.3	V
Operating temperature range	Topr	–40 to 85	°C
Storage temperature range	Tstg	–55 to +125	°C
Temperature under bias	Tbias	–40 to +85	°C

DC Operating Conditions (Ta = –40 to +85°C)

Parameter	Symbol	Min	Type	Max	Unit
Supply voltage	V_{DD}	3.0	3.3	3.6	V
	V_{SS}	0	0	0	V
Input high voltage	V_{IH}	2.2	—	V_{DD} + 0.3	V
Input low voltage	V_{IL}	–0.3	—	0.8	V

DC Characteristics (V_{DD} = 3.3 V ± 0.3 V, V_{SS} = 0 V, Ta = –40 to +85°C)

Parameter	Symbol	Min	Max	Unit	Test conditions
Operating V_{DD} current	I_{DD}	—	60	mA	V_{DD} = 3.6 V, I_{DOUT} = 0 mA, t_{RC} = 120 ns
Standby V_{DD} current	I_{SB1}	—	30	µA	V_{DD} = 3.6 V, $\overline{CE} \geq V_{DD}$ –0.2 V
	I_{SB2}	—	3	mA	V_{DD} = 3.6 V, $\overline{CE}$ = 2.2 V
Input leakage current	$\|I_{IL}\|$	—	10	µA	Vin = 0 to V_{DD}
Output leakage current	$\|I_{OL}\|$	—	10	µA	$\overline{CE}$ = 2.2 V, V_{OUT} = 0 to V_{DD}
Output high voltage	V_{OH}	2.4	—	V	I_{OH} = –2.0 mA
Output low voltage	V_{OL}	—	0.4	V	I_{OL} = 2.0 mA

Capacitance (V_{DD} = 3.3 V ± 0.3 V, V_{SS} = 0 V, Ta = 25°C, Vin = 0 V, f = 1 MHz)

Parameter	Symbol	Min	Max	Unit
Input capacitance	Cin	—	10	pF
Output capacitance	Cout	—	15	pF

AC Characteristics (V_{DD} = 3.3 V ± 0.3 V, V_{SS} = 0 V, Ta = –40 to + 85°C)

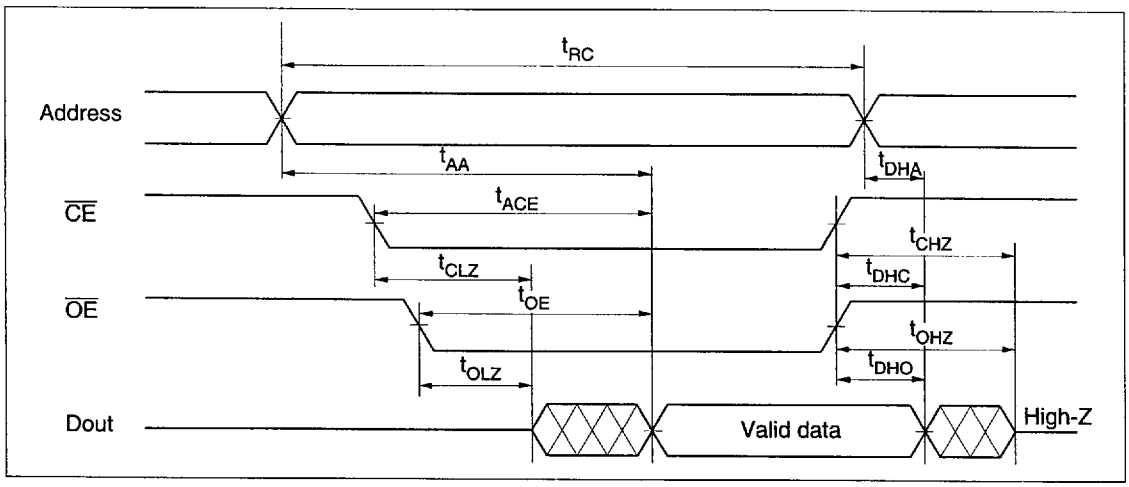
- Input pulse levels: 0.4 to 2.4 V
- Input rise and fall time: 5 ns
- Input and output timing reference levels: 1.4 V
- Output load: 1TTL + C_L = 50 pF (including jig)

		HN62W448NI-12			
Parameter	**Symbol**	**Min**	**Max**	**Unit**	Notes
Read cycle time	t_{RC}	120	—	ns	
Page read cycle time	t_{PC}	50	—	ns	
Address access time	t_{AA}	—	120	ns	3
Page address access time	t_{PA}	—	50	ns	
$\overline{CE}$ access time	t_{ACE}	—	120	ns	3
$\overline{OE}$ access time	t_{OE}	—	50	ns	3
BHE access time	t_{BHE}	—	120	ns	
Output hold time from address change	t_{DHA}	0	—	ns	2
Output hold time from $\overline{CE}$	t_{DHC}	0	—	ns	2
Output hold time from $\overline{OE}$	t_{DHO}	0	—	ns	2
Output hold time from BHE	t_{DHB}	0	—	ns	
$\overline{CE}$ to output in high-Z	t_{CHZ}	—	50	ns	1
$\overline{OE}$ to output in high-Z	t_{OHZ}	—	50	ns	1
BHE to output in high-Z	t_{BHZ}	—	50	ns	1
$\overline{CE}$ to output in low-Z	t_{CLZ}	5	—	ns	4
$\overline{OE}$ to output in low-Z	t_{OLZ}	5	—	ns	4
BHE to output in low-Z	t_{BLZ}	5	—	ns	

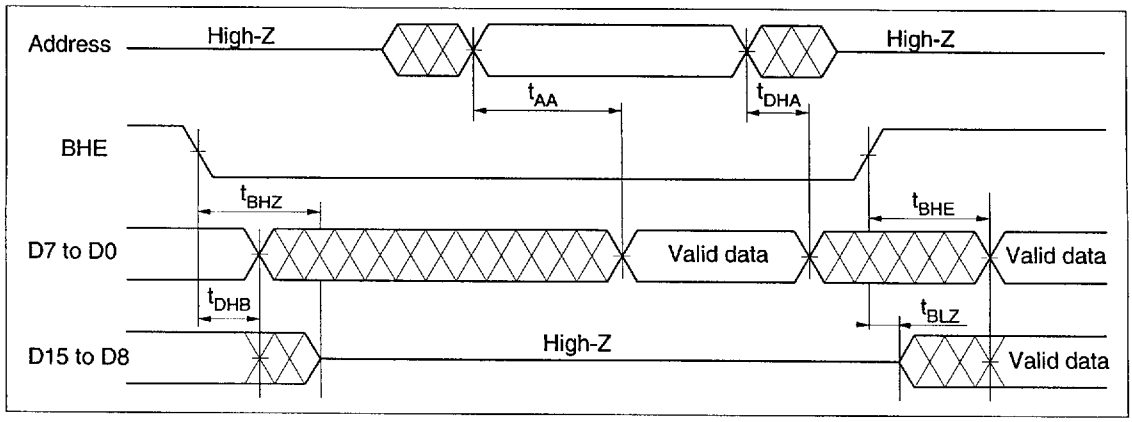
Notes:
1. t_{CHZ}, t_{OHZ} and t_{BHZ} are defined as the time at which the output achieves the open circuit conditions and are not referred to output voltage levels.
2. t_{DHA}, t_{DHC}, t_{DHO}: Determined by faster.
3. t_{AA}, t_{ACE}, t_{OE}: Determined by slower.
4. t_{CLZ}, t_{OLZ}: Determined by slower.
5. $\overline{CE}$ and $\overline{OE}$ are enable A18 to A0 are valid.
6. D15/A-1 pin is in the output state when BHE is high, $\overline{CE}$ and $\overline{OE}$ are enable. Therefore, the input signals of opposite phase to the output must be applied to them.
7. Page address is determined as below.
   Word mode (BHE = 'V_{IH}'): A0, A1
   Byte mode (BHE = 'V_{IL}'): A-1, A0, A1
8. $\overline{CE}$ and $\overline{OE}$ are enable.
9. This device is used ATD (Address Transient Detector). Therefore, transfer either $\overline{CE}$ or address (A2 to A18) after power up to 3.0 V.

Timing Waveforms

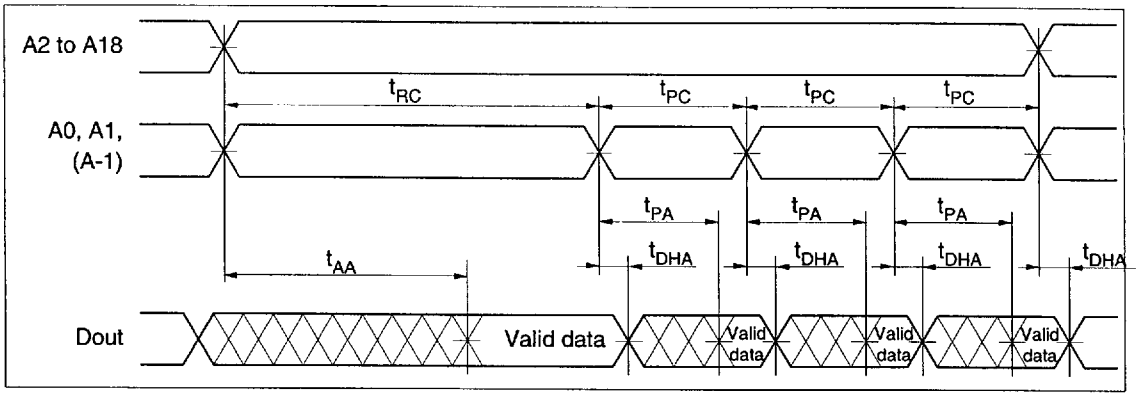
Word Mode (BHE = 'V_{IH}') **or Byte Mode** (BHE = 'V_{IL}')*[2, 3, 4]



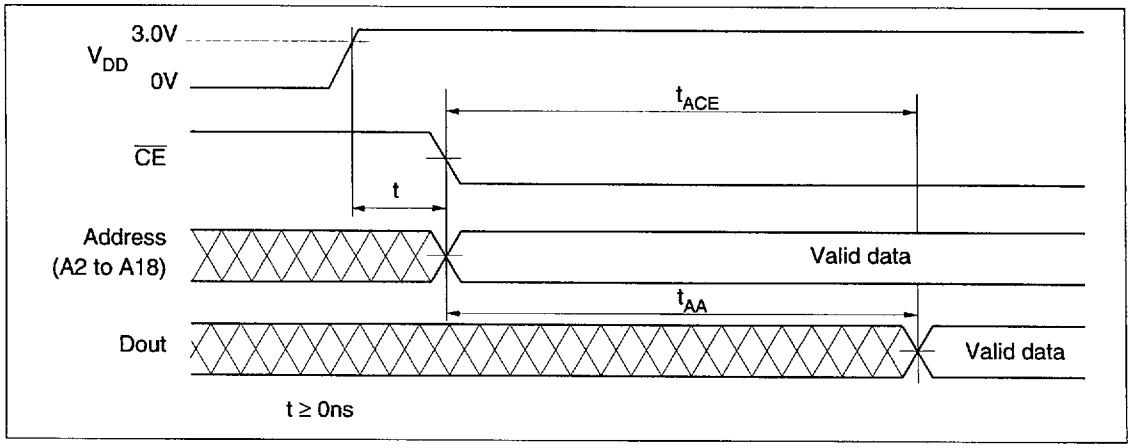
Word Mode, Byte Mode Switch*[5, 6]



Page Mode[*7, 8]



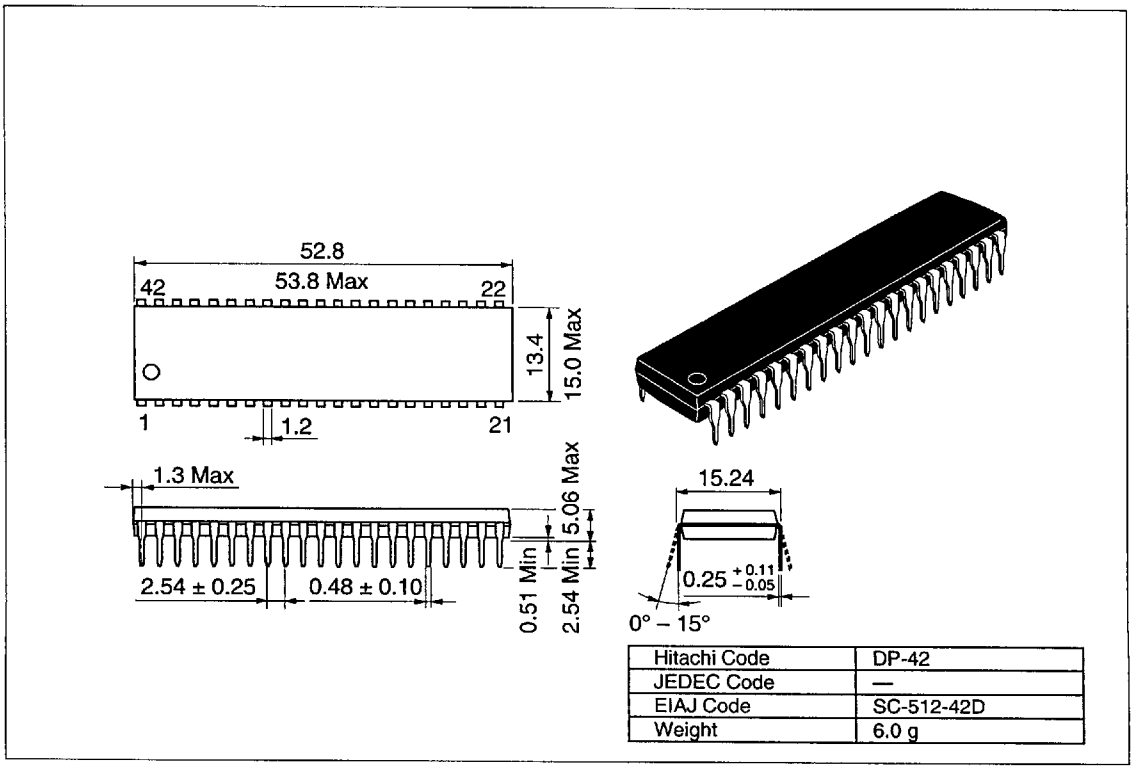
Power Up Sequence[*9]



Package Dimensions

HN62W448NPI Series (DP-42)

Unit: mm

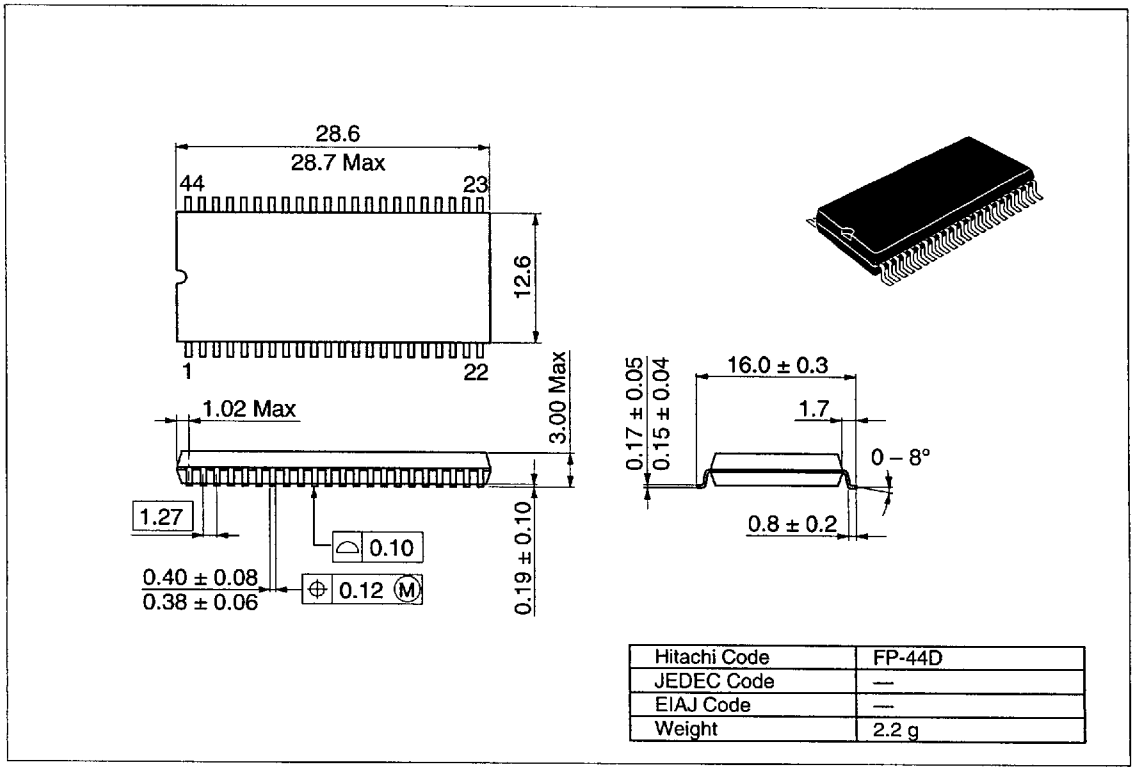


Hitachi Code	DP-42
JEDEC Code	—
EIAJ Code	SC-512-42D
Weight	6.0 g

Package Dimensions (cont.)

HN62W448NFBI Series (FP-44D)

Unit: mm



Hitachi Code	FP-44D
JEDEC Code	—
EIAJ Code	—
Weight	2.2 g

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Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
1.0	Apr. 22, 1997	Initial issue		